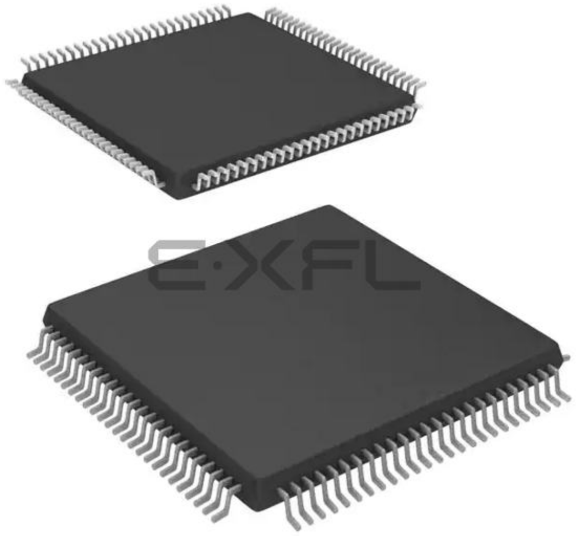
Microchip Technology - A3PN250-Z1VQG100 Datasheet



Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	68
Number of Gates	250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-20°C ~ 85°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pn250-z1vqg100

Table 2-1 **• ProASIC3/E/nano Low Power Modes Summary**

Mode	Power Supplies / Clock Status	Needed to Start Up
Active	On – All, clock Off – None	N/A (already active)
Static (Idle)	On – All Off – No active clock in FPGA Optional: Enter User Low Static (Idle) Mode by enabling ULSICC macro to further reduce power consumption by powering down FlashROM.	Initiate clock source. No need to initialize volatile contents.
Sleep	On – VCCI Off – VCC (core voltage), VJTAG (JTAG DC voltage), and VPUMP (programming voltage) LAPU enables immediate operation when power returns. Optional: Save state of volatile contents in external memory.	Need to turn on core. Load states from external memory. As needed, restore volatile contents from external memory.
Shutdown	On – None Off – All power supplies Applicable to all ProASIC3 nano devices, cold-sparing and hot-insertion allow the device to be powered down without bringing down the system. LAPU enables immediate operation when power returns.	Need to turn on VCC, VCCI.

Static (Idle) Mode

In Static (Idle) mode, the clock inputs are not switching and the static power consumption is the minimum power required to keep the device powered up. In this mode, I/Os are only drawing the minimum leakage current specified in the datasheet. Also, in Static (Idle) mode, embedded SRAM, I/Os, and registers retain their values, so the device can enter and exit this mode without any penalty.

If the embedded PLLs are used as the clock source, Static (Idle) mode can be entered easily by pulling LOW the PLL POWERDOWN pin (active-low). By pulling the PLL POWERDOWN pin to LOW, the PLL is turned off. Refer to Figure 2-1 on page 23 for more information.

Alternatively, Figure 2-7 shows how a microprocessor can be used with a voltage regulator's shutdown pin to turn the power supplies connected to the device on or off.

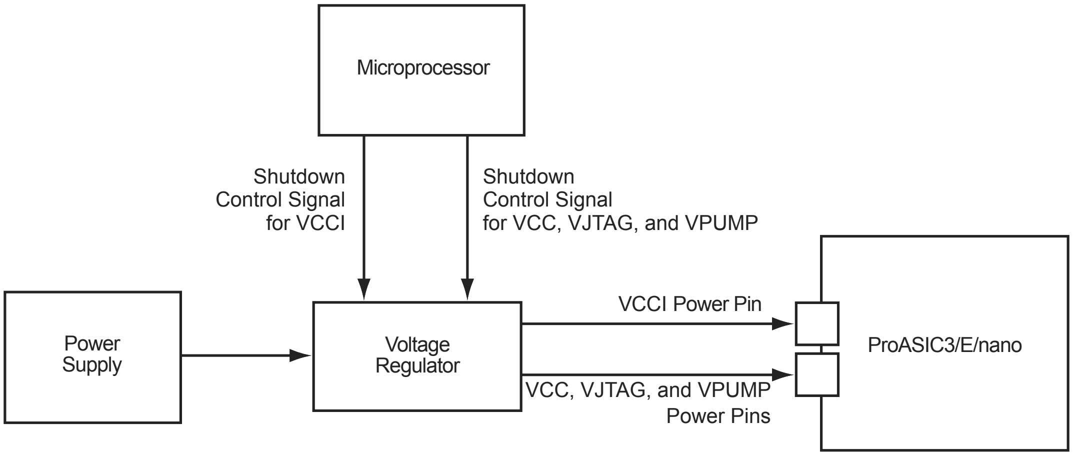


Figure 2-7 • **Controlling Power On/Off State Using Microprocessor and Voltage Regulator**

Though Sleep mode or Shutdown mode can be used to save power, the content of the SRAM and the state of the registers is lost when power is turned off if no other measure is taken. To keep the original contents of the device, a low-cost external serial EEPROM can be used to save and restore the device contents when entering and exiting Sleep mode. In the *Embedded SRAM Initialization Using External Serial EEPROM* application note, detailed information and a reference design are provided to initialize the embedded SRAM using an external serial EEPROM. The user can easily customize the reference design to save and restore the FPGA state when entering and exiting Sleep mode. The microcontroller will need to manage this activity, so before powering down VCC, the data must be read from the FPGA and stored externally. Similarly, after the FPGA is powered up, the microcontroller must allow the FPGA to load the data from external memory and restore its original state.

Conclusion

Microsemi ProASIC3/E and ProASIC3 nano FPGAs inherit low power consumption capability from their nonvolatile and live-at-power-up flash-based technology. Power consumption can be reduced further using the Static (Idle), User Low Static (Idle), Sleep, or Shutdown power modes. All these features result in a low-power, cost-effective, single-chip solution designed specifically for power-sensitive electronics applications.

Related Documents

Application Notes

Embedded SRAM Initialization Using External Serial EEPROM

http://www.microsemi.com/soc/documents/EmbeddedSRAMInit_AN.pdf

Using Spines of Occupied Global Networks

When a signal is assigned to a global network, the flash switches are programmed to set the MUX select lines (explained in the "Clock Aggregation Architecture" section on page 45) to drive the spines of that network with the global net. However, if the global net is restricted from reaching into the scope of a spine, the MUX drivers of that spine are available for other high-fanout or critical signals (Figure 3-20).

For example, if you want to limit the CLK1_c signal to the left half of the chip and want to use the right side of the same global network for CLK2_c, you can add the following PDC commands:

```
define_region -name region1 -type inclusive 0 0 34 29
assign_net_macros region1 CLK1_c
assign_local_clock –net CLK2_c –type chip B2
```

Figure 3-20 • **Design Example Using Spines of Occupied Global Networks**

Conclusion

IGLOO, Fusion, and ProASIC3 devices contain 18 global networks: 6 chip global networks and 12 quadrant global networks. These global networks can be segmented into local low-skew networks called spines. The spines provide low-skew networks for the high-fanout signals of a design. These allow you up to 252 different internal/external clocks in an A3PE3000 device. This document describes the architecture for the global network, plus guidelines and methodologies in assigning signals to globals and spines.

Related Documents

User’s Guides

IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide

http://www.microsemi.com/soc/documents/pa3_libguide_ug.pdf

Fusion CCC Locations

Fusion devices have six CCCs: one in each of the four corners and one each in the middle of the east and west sides of the device (Figure 4-17 and Figure 4-18). The device can have one integrated PLL in the middle of the west side of the device or two integrated PLLs in the middle of the east and west sides of the device (middle right and middle left).

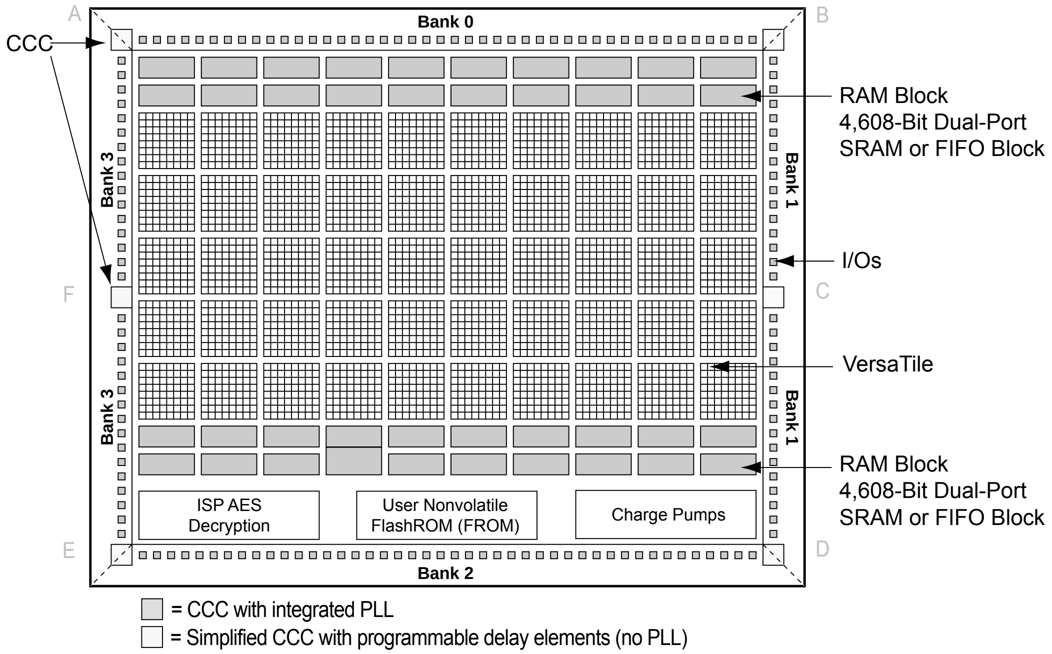


Figure 4-17 • **CCC Locations in Fusion Family Devices (AFS090, AFS250, M1AFS250)**

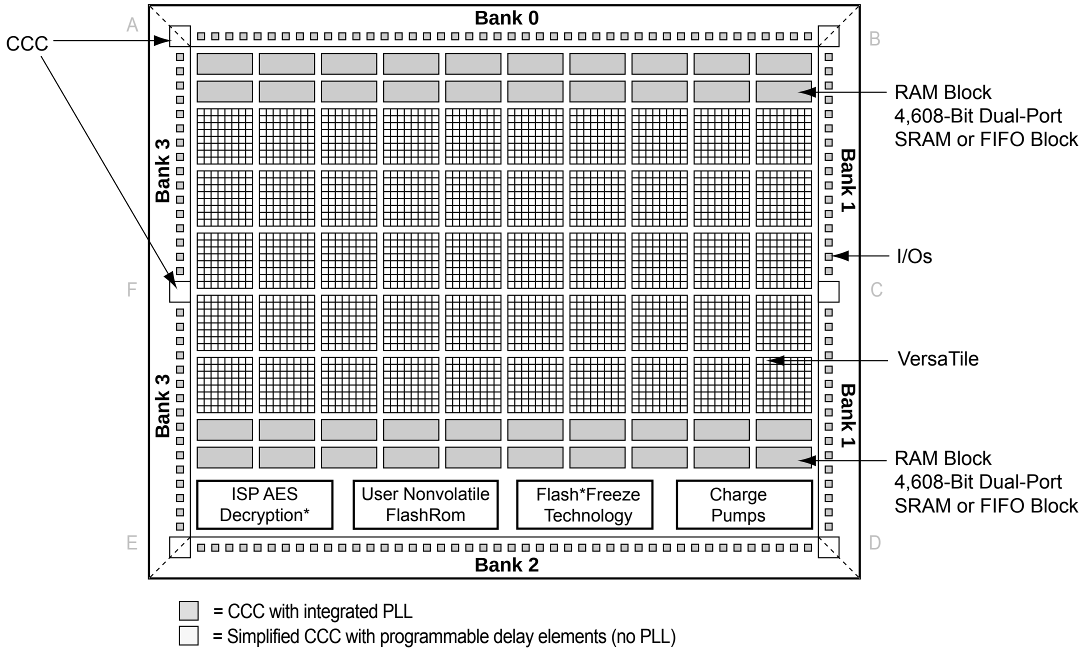


Figure 4-18 • **CCC Locations in Fusion Family Devices (except AFS090, AFS250, M1AFS250)**

PLL Core Specifications

PLL core specifications can be found in the DC and Switching Characteristics chapter of the appropriate family datasheet.

Loop Bandwidth

Common design practice for systems with a low-noise input clock is to have PLLs with small loop bandwidths to reduce the effects of noise sources at the output. Table 4-6 shows the PLL loop bandwidth, providing a measure of the PLL's ability to track the input clock and jitter.

Table 4-6 **• –3 dB Frequency of the PLL**

	Minimum (T_a = +125°C, VCCA = 1.4 V)	**Typical (T_a = +25°C, VCCA = 1.5 V)**	**Maximum (T_a = –55°C, VCCA = 1.6 V)**
–3 dB Frequency	15 kHz	25 kHz	45 kHz

PLL Core Operating Principles

This section briefly describes the basic principles of PLL operation. The PLL core is composed of a phase detector (PD), a low-pass filter (LPF), and a four-phase voltage-controlled oscillator (VCO). Figure 4-19 illustrates a basic single-phase PLL core with a divider and delay in the feedback path.

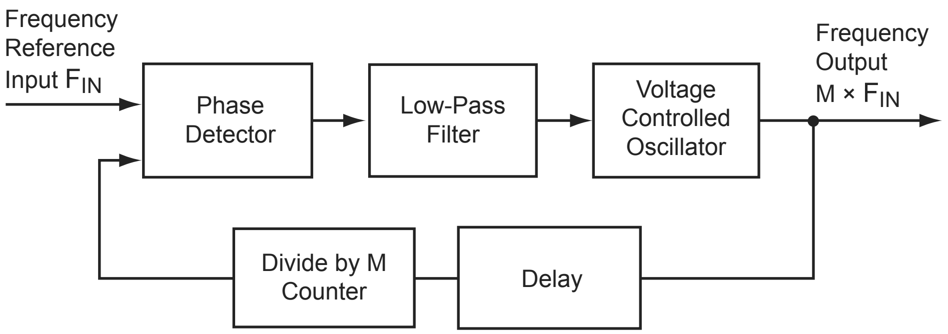


Figure 4-19 **• Simplified PLL Core with Feedback Divider and Delay**

The PLL is an electronic servo loop that phase-aligns the PD feedback signal with the reference input. To achieve this, the PLL dynamically adjusts the VCO output signal according to the average phase difference between the input and feedback signals.

The first element is the PD, which produces a voltage proportional to the phase difference between its inputs. A simple example of a digital phase detector is an Exclusive-OR gate. The second element, the LPF, extracts the average voltage from the phase detector and applies it to the VCO. This applied voltage alters the resonant frequency of the VCO, thus adjusting its output frequency.

Consider Figure 4-19 with the feedback path bypassing the divider and delay elements. If the LPF steadily applies a voltage to the VCO such that the output frequency is identical to the input frequency, this steady-state condition is known as lock. Note that the input and output phases are also identical. The PLL core sets a LOCK output signal HIGH to indicate this condition.

Should the input frequency increase slightly, the PD detects the frequency/phase difference between its reference and feedback input signals. Since the PD output is proportional to the phase difference, the change causes the output from the LPF to increase. This voltage change increases the resonant frequency of the VCO and increases the feedback frequency as a result. The PLL dynamically adjusts in this manner until the PD senses two phase-identical signals and steady-state lock is achieved. The opposite (decreasing PD output signal) occurs when the input frequency decreases.

Now suppose the feedback divider is inserted in the feedback path. As the division factor M (shown in Figure 4-20 on page 85) is increased, the average phase difference increases. The average phase

When SmartGen is used to define the configuration that will be shifted in via the serial interface, SmartGen prints out the values of the 81 configuration bits. For ease of use, several configuration bits are automatically inferred by SmartGen when the dynamic PLL core is generated; however, <71:73> (STATASEL, STATBSEL, STATCSEL) and <77:79> (DYNASEL, DYNBSEL, DYNCSEL) depend on the input clock source of the corresponding CCC. Users must first run Layout in Designer to determine the exact setting for these ports. After Layout is complete, generate the "CCC_Configuration" report by choosing **Tools** > **Reports** > **CCC_Configuration** in the Designer software. Refer to "PLL Configuration Bits Description" on page 90 for descriptions of the PLL configuration bits. For simulation purposes, bits <71:73> and <78:80> are "don't care." Therefore, it is strongly suggested that SmartGen be used to generate the correct configuration bit settings for the dynamic PLL core.

After setting all the required parameters, users can generate one or more PLL configurations with HDL or EDIF descriptions by clicking the **Generate** button. SmartGen gives the option of saving session results and messages in a log file:

```
****************
Macro Parameters
****************

Name                            : dyn_pll_hardio
Family                          : ProASIC3E
Output Format                   : VERILOG
Type                            : Dynamic CCC
Input Freq(MHz)                 : 30.000
CLKA Source                     : Hardwired I/O
Feedback Delay Value Index      : 1
Feedback Mux Select             : 1
XDLY Mux Select                 : No
Primary Freq(MHz)               : 33.000
Primary PhaseShift              : 0
Primary Delay Value Index       : 1
Primary Mux Select              : 4
Secondary1 Freq(MHz)            : 40.000
Use GLB                         : YES
Use YB                          : NO
GLB Delay Value Index           : 1
YB Delay Value Index            : 1
Secondary1 PhaseShift           : 0
Secondary1 Mux Select           : 0
Secondary1 Input Freq(MHz)      : 40.000
CLKB Source                     : Hardwired I/O
Secondary2 Freq(MHz)            : 50.000
Use GLC                         : YES
Use YC                          : NO
GLC Delay Value Index           : 1
YC Delay Value Index            : 1
Secondary2 PhaseShift           : 0
Secondary2 Mux Select           : 0
Secondary2 Input Freq(MHz)      : 50.000
CLKC Source                     : Hardwired I/O

Configuration Bits:
FINDIV[6:0]     0000101
FBDIV[6:0]      0100000
OADIV[4:0]      00100
OBDIV[4:0]      00000
OCDIV[4:0]      00000
OAMUX[2:0]      100
OBMUX[2:0]      000
OCMUX[2:0]      000
FBSEL[1:0]      01
FBDLY[4:0]      00000
XDLYSEL         0
DLYGLA[4:0]     00000
DLYGLB[4:0]     00000
```

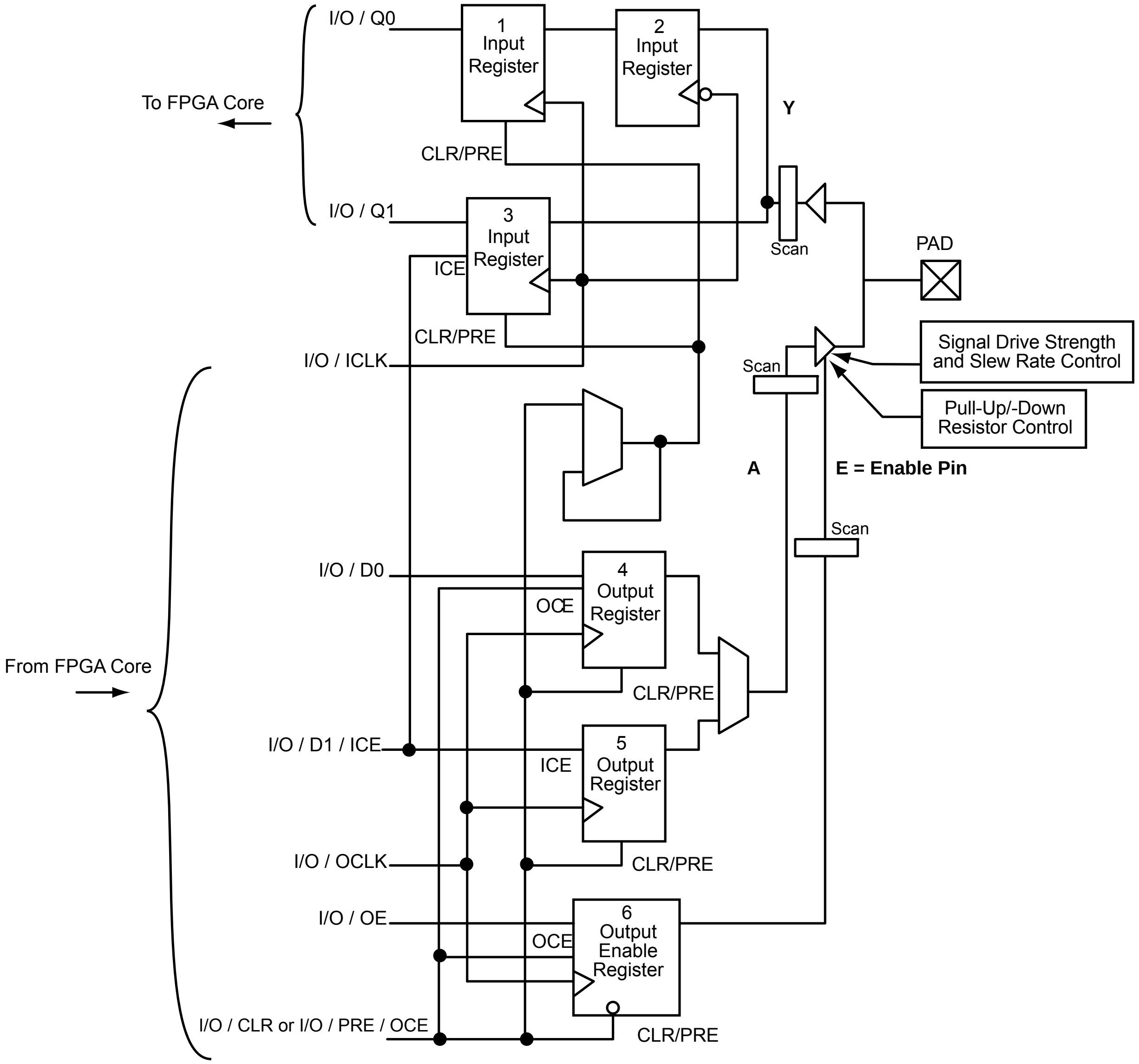


Figure 7-2 • **I/O Block Logical Representation for Dual-Tile Designs (60 k,125 k, and 250 k Devices)**

Low Power Flash Device I/O Support

The low power flash families listed in Table 7-1 support I/Os and the functions described in this document.

Table 7-1 **• Flash-Based FPGAs**

Series	Family*	Description
IGLOO	IGLOO nano	Lowest power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
ProASIC3	ProASIC3 nano	Lowest cost 1.5 V FPGAs with balanced performance

*Note: *The device name links to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.*

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 7-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 7-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

Cold-Sparing Support

Cold-sparing refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Cold-sparing is supported on all IGLOO nano and ProASIC3 nano devices only when the user provides resistors from each power supply to ground. The resistor value is calculated based on the decoupling capacitance on a given power supply. The RC constant should be greater than 3 µs.

To remove resistor current during operation, it is suggested that the resistor be disconnected (e.g., with an NMOS switch) from the power supply after the supply has reached its final value. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 307 for details on cold-sparing.

Cold-sparing means that a subsystem with no power applied (usually a circuit board) is electrically connected to the system that is in operation. This means that all input buffers of the subsystem must present very high input impedance with no power applied so as not to disturb the operating portion of the system.

When targeting low power applications, I/O cold-sparing may add additional current if a pin is configured with either a pull-up or pull-down resistor and driven in the opposite direction. A small static current is induced on each I/O pin when the pin is driven to a voltage opposite to the weak pull resistor. The current is equal to the voltage drop across the input pin divided by the pull resistor. Refer to the "Detailed I/O DC Characteristics" section of the appropriate family datasheet for the specific pull resistor value for the corresponding I/O standard.

For example, assuming an LVTTL 3.3 V input pin is configured with a weak pull-up resistor, a current will flow through the pull-up resistor if the input pin is driven LOW. For LVTTL 3.3 V, the pull-up resistor is ~45 kΩ, and the resulting current is equal to 3.3 V / 45 kΩ = 73 µA when the I/O pin is driven LOW. This is true also when a weak pull-down is chosen and the input pin is driven HIGH. This current can be avoided by driving the input Low when a weak pull-down resistor is used and driving it HIGH when a weak pull-up resistor is used.

This current draw can occur in the following cases:

- In Active and Static modes:
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High
  - Output buffers with pull-up, driven Low
  - Output buffers with pull-down, driven High
  - Tristate buffers with pull-up, driven Low
  - Tristate buffers with pull-down, driven High
- In Flash*Freeze mode (not supported on ProASIC3 nano devices):
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High

Electrostatic Discharge Protection

Low power flash devices are tested per JEDEC Standard JESD22-A114-B.

These devices contain clamp diodes at every I/O, global, and power pad. Clamp diodes protect all device pads against damage from ESD as well as from excessive voltage transients.

All nano devices are qualified to the Human Body Model (HBM) and the Charged Device Model (CDM).

Table 7-12 • **I/O Hot-Swap and 5 V Input Tolerance Capabilities in nano Devices**

I/O Assignment	Clamp Diode	Hot Insertion	5 V Input Tolerance	Input Buffer	Output Buffer
3.3 V LVTTL/LVCMOS	No	Yes	Yes*	Enabled/Disabled	
LVCMOS 2.5 V	No	Yes	No	Enabled/Disabled	
LVCMOS 1.8 V	No	Yes	No	Enabled/Disabled	
LVCMOS 1.5 V	No	Yes	No	Enabled/Disabled	
LVCMOS 1.2 V	No	Yes	No	Enabled/Disabled	

* *Can be implemented with an external IDT bus switch, resistor divider, or Zener with resistor.*

5 V Input and Output Tolerance

nano devices can be made 5 V–input–tolerant for certain I/O standards by using external level shifting techniques. 5 V output compliance can be achieved using certain I/O standards.

Table 7-5 on page 163 shows the I/O standards that support 5 V input tolerance. Only 3.3 V LVTTL/LVCMOS standards support 5 V output tolerance.

5 V Input Tolerance

I/Os can support 5 V input tolerance when LVTTL 3.3 V or LVCMOS 3.3 V configurations are used (see Table 7-12). There are three recommended solutions for achieving 5 V receiver tolerance (see Figure 7-5 on page 172 to Figure 7-7 on page 173 for details of board and macro setups). All the solutions meet a common requirement of limiting the voltage at the input to 3.6 V or less. In fact, the I/O absolute maximum voltage rating is 3.6 V, and any voltage above 3.6 V may cause long-term gate oxide failures.

Solution 1

The board-level design must ensure that the reflected waveform at the pad does not exceed the limits provided in the recommended operating conditions in the datasheet. This is a requirement to ensure long-term reliability.

This solution requires two board resistors, as demonstrated in Figure 7-5 on page 172. Here are some examples of possible resistor values (based on a simplified simulation model with no line effects and 10 Ω transmitter output resistance, where Rtx_out_high = (VCCI – VOH) / I_{OH} and Rtx_out_low = VOL / I_{OL}).

Example 1 (high speed, high current):

Rtx_out_high = Rtx_out_low = 10 Ω

R1 = 36 Ω (±5%), P(r1)min = 0.069 Ω

R2 = 82 Ω (±5%), P(r2)min = 0.158 Ω

Imax_tx = 5.5 V / (82 × 0.95 + 36 × 0.95 + 10) = 45.04 mA

$t_{RISE} = t_{FALL}$ = 0.85 ns at C_pad_load = 10 pF (includes up to 25% safety margin)

$t_{RISE} = t_{FALL}$ = 4 ns at C_pad_load = 50 pF (includes up to 25% safety margin)

Example 2 (low–medium speed, medium current):

Rtx_out_high = Rtx_out_low = 10 Ω

R1 = 220 Ω (±5%), P(r1)min = 0.018 Ω

R2 = 390 Ω (±5%), P(r2)min = 0.032 Ω

Imax_tx = 5.5 V / (220 × 0.95 + 390 × 0.95 + 10) = 9.17 mA

$t_{RISE} = t_{FALL}$ = 4 ns at C_pad_load = 10 pF (includes up to 25% safety margin)

$t_{RISE} = t_{FALL}$ = 20 ns at C_pad_load = 50 pF (includes up to 25% safety margin)

Other values of resistors are also allowed as long as the resistors are sized appropriately to limit the voltage at the receiving end to 2.5 V < Vin (rx) < 3.6 V when the transmitter sends a logic 1. This range of Vin_dc(rx) must be assured for any combination of transmitter supply (5 V ± 0.5 V), transmitter output resistance, and board resistor tolerances.

Temporary overshoots are allowed according to the overshoot and undershoot table in the datasheet.

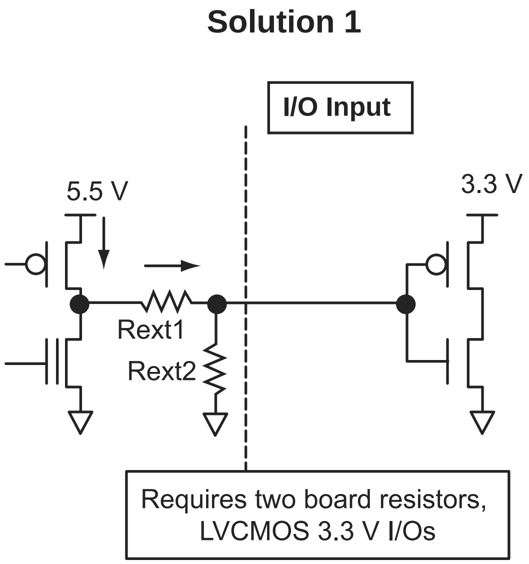


Figure 7-5 • **Solution 1**

3. Double-click I/O to open the Create Core window, which is shown in Figure 8-3).

Figure 8-3 **• I/O Create Core Window**

As seen in Figure 8-3, there are five tabs to configure the I/O macro: Input Buffers, Output Buffers, Bidirectional Buffers, Tristate Buffers, and DDR.

Input Buffers

There are two variations: Regular and Special.

If the **Regular** variation is selected, only the Width (1 to 128) needs to be entered. The default value for Width is 1.

The **Special** variation has Width, Technology, Voltage Level, and Resistor Pull-Up/-Down options (see Figure 8-3). All the I/O standards and supply voltages (V_{CCI}) supported for the device family are available for selection.

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
	Notes were added where appropriate to point out that IGLOO nano and ProASIC3 nano devices do not support differential inputs (SAR 21449).	N/A
v1.4 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 9-1 • Flash-Based FPGAs.	206
	The "I/O Cell Architecture" section was updated with information applicable to nano devices.	207
	The output buffer (OUTBUF_SSTL3_I) input was changed to D, instead of Q, in Figure 9-1 • DDR Support in Low Power Flash Devices, Figure 9-3 • DDR Output Register (SSTL3 Class I), Figure 9-6 • DDR Output Register (SSTL3 Class I), Figure 9-7 • DDR Tristate Output Register, LOW Enable, 8 mA, Pull-Up (LVTTL), and the output from the DDR_OUT macro was connected to the input of the TRIBUFF macro in Figure 9-7 • DDR Tristate Output Register, LOW Enable, 8 mA, Pull-Up (LVTTL).	205, 209, 212, 213
v1.3 (October 2008)	The "Double Data Rate (DDR) Architecture" section was updated to include mention of the AFS600 and AFS1500 devices.	205
	The "DDR Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	206
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 9-1 • Flash-Based FPGAs: • ProASIC3L was updated to include 1.5 V. • The number of PLLs for ProASIC3E was changed from five to six.	206
v1.1 (March 2008)	The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	206

11 – Security in Low Power Flash Devices

Security in Programmable Logic

The need for security on FPGA programmable logic devices (PLDs) has never been greater than today. If the contents of the FPGA can be read by an external source, the intellectual property (IP) of the system is vulnerable to unauthorized copying. Fusion, IGLOO, and ProASIC3 devices contain state-of-the-art circuitry to make the flash-based devices secure during and after programming. Low power flash devices have a built-in 128-bit Advanced Encryption Standard (AES) decryption core (except for 30 k gate devices and smaller). The decryption core facilitates secure in-system programming (ISP) of the FPGA core array fabric, the FlashROM, and the Flash Memory Blocks (FBs) in Fusion devices. The FlashROM, Flash Blocks, and FPGA core fabric can be programmed independently of each other, allowing the FlashROM or Flash Blocks to be updated without the need for change to the FPGA core fabric.

Microsemi has incorporated the AES decryption core into the low power flash devices and has also included the Microsemi flash-based lock technology, FlashLock.® Together, they provide leading-edge security in a programmable logic device. Configuration data loaded into a device can be decrypted prior to being written to the FPGA core using the AES 128-bit block cipher standard. The AES encryption key is stored in on-chip, nonvolatile flash memory.

This document outlines the security features offered in low power flash devices, some applications and uses, as well as the different software settings for each application.

Figure 11-1 • **Overview on Security**

Figure 12-2 shows different applications for ISP programming.

1. In a trusted programming environment, you can program the device using the unencrypted (plaintext) programming file.
2. You can program the AES Key in a trusted programming environment and finish the final programming in an untrusted environment using the AES-encrypted (cipher text) programming file.
3. For the remote ISP updating/reprogramming, the AES Key stored in the device enables the encrypted programming bitstream to be transmitted through the untrusted network connection.

Microsemi low power flash devices also provide the unique Microsemi FlashLock feature, which protects the Pass Key and AES Key. Unless the original FlashLock Pass Key is used to unlock the device, security settings cannot be modified. Microsemi does not support read-back of FPGA core-programmed data; however, the FlashROM contents can selectively be read back (or disabled) via the JTAG port based on the security settings established by the Microsemi Designer software. Refer to the "Security in Low Power Flash Devices" section on page 235 for more information.

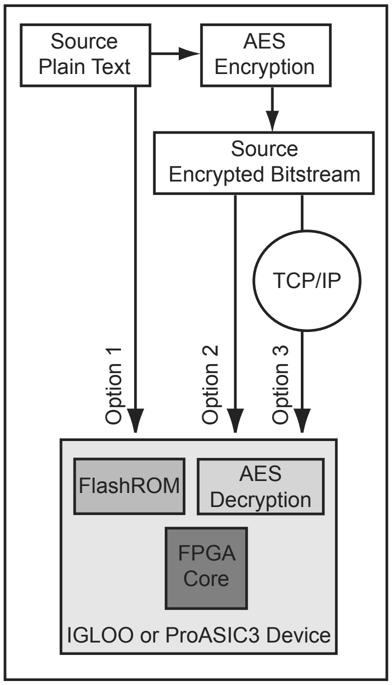


Figure 12-2 • **Different ISP Use Models**

FlashROM and Programming Files

Each low power flash device has 1 kbit of on-chip, nonvolatile flash memory that can be accessed from the FPGA core. This nonvolatile FlashROM is arranged in eight pages of 128 bits (Figure 12-3). Each page can be programmed independently, with or without the 128-bit AES encryption. The FlashROM can only be programmed via the IEEE 1532 JTAG port and cannot be programmed from the FPGA core. In addition, during programming of the FlashROM, the FPGA core is powered down automatically by the on-chip programming control logic.

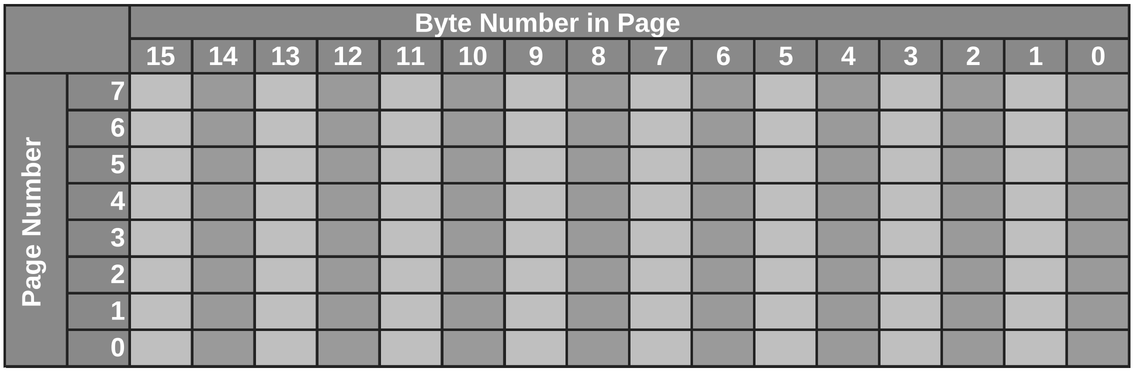


***Figure 12-3* • FlashROM Architecture**

When using FlashROM combined with AES, many subscription-based applications or device serialization applications are possible. The FROM configurator found in the Libero SoC Catalog supports easy management of the FlashROM contents, even over large numbers of devices. The FROM configurator can support FlashROM contents that contain the following:

- Static values
- Random numbers
- Values read from a file
- Independent updates of each page

In addition, auto-incrementing of fields is possible. In applications where the FlashROM content is different for each device, you have the option to generate a single STAPL file for all the devices or individual serialization files for each device. For more information on how to generate the FlashROM content for device serialization, refer to the "FlashROM in Microsemi's Low Power Flash Devices" section on page 117.

Libero SoC includes a unique tool to support the generation and management of FlashROM and FPGA programming files. This tool is called FlashPoint.

Depending on the applications, designers can use the FlashPoint software to generate a STAPL file with different contents. In each case, optional AES encryption and/or different security settings can be set.

In Designer, when you click the Programming File icon, FlashPoint launches, and you can generate STAPL file(s) with four different cases (Figure 12-4 on page 268). When the serialization feature is used during the configuration of FlashROM, you can generate a single STAPL file that will program all the devices or an individual STAPL file for each device.

The following cases present the FPGA core and FlashROM programming file combinations that can be used for different applications. In each case, you can set the optional security settings (FlashLock Pass Key and/or AES Key) depending on the application.

1. A single STAPL file or multiple STAPL files with multiple FlashROM contents and the FPGA core content. A single STAPL file will be generated if the device serialization feature is not used. You can program the whole FlashROM or selectively program individual pages.
2. A single STAPL file for the FPGA core content

Circuit Verification

The power switching circuit recommended above is implemented on Microsemi's Icicle board (Figure 13-2). On the Icicle board, VJTAGENB is used to control the N-Channel Digital FET; however, this circuit was modified to use TRST instead of VJTAGENB in this application. There are three important aspects of this circuit that were verified:

1. The rise on VCC from 1.2 V to 1.5 V when TRST is HIGH
2. VCC rises to 1.5 V before programming begins.
3. VCC switches from 1.5 V to 1.2 V when TRST is LOW.

Verification Steps

1. The rise on VCC from 1.2 V to 1.5 V when TRST is HIGH.

Figure 13-2 • **Core Voltage on the IGLOO AGL125-QNG132 Device**

In the oscilloscope plots (Figure 13-2), the TRST from FlashPro3 and the VCC core voltage of the IGLOO device are labeled. This plot shows the rise characteristic of the TRST signal from FlashPro3. Once the TRST signal is asserted HIGH, the LTC3025 shown in Figure 13-1 on page 277 senses the increase in voltage and changes the output from 1.2 V to 1.5 V. It takes the circuit approximately 100 µs to respond to TRST and change the voltage to 1.5 V on the VCC core.

Boundary Scan Support in Low Power Devices

The information in this document applies to all Fusion, IGLOO, and ProASIC3 devices. For IGLOO, IGLOO PLUS, and ProASIC3L devices, the Flash*Freeze pin must be deasserted for successful boundary scan operations. Devices cannot enter JTAG mode directly from Flash*Freeze mode.

Boundary Scan Opcodes

Low power flash devices support all mandatory IEEE 1149.1 instructions (EXTEST, SAMPLE/PRELOAD, and BYPASS) and the optional IDCODE instruction (Table 15-2).

***Table 15-2* • Boundary Scan Opcodes**

	Hex Opcode
EXTEST	00
HIGHZ	07
USERCODE	0E
SAMPLE/PRELOAD	01
IDCODE	0F
CLAMP	05
BYPASS	FF

Boundary Scan Chain

The serial pins are used to serially connect all the boundary scan register cells in a device into a boundary scan register chain (Figure 15-2 on page 294), which starts at the TDI pin and ends at the TDO pin. The parallel ports are connected to the internal core logic I/O tile and the input, output, and control ports of an I/O buffer to capture and load data into the register to control or observe the logic state of each I/O.

Each test section is accessed through the TAP, which has five associated pins: TCK (test clock input), TDI, TDO (test data input and output), TMS (test mode selector), and TRST (test reset input). TMS, TDI, and TRST are equipped with pull-up resistors to ensure proper operation when no input data is supplied to them. These pins are dedicated for boundary scan test usage. Refer to the "JTAG Pins" section in the "Pin Descriptions and Packaging" chapter of the appropriate device datasheet for pull-up/-down recommendations for TCK and TRST pins. Pull-down recommendations are also given in Table 15-3 on page 294

Internal Pull-Up and Pull-Down

Low power flash device I/Os are equipped with internal weak pull-up/-down resistors that can be used by designers. If used, these internal pull-up/-down resistors will be activated during power-up, once both VCC and VCCI are above their functional activation level. Similarly, during power-down, these internal pull-up/-down resistors will turn off once the first supply voltage falls below its brownout deactivation level.

Cold-Sparing

In cold-sparing applications, voltage can be applied to device I/Os before and during power-up. Cold-sparing applications rely on three important characteristics of the device:

1. I/Os must be tristated before and during power-up.
2. Voltage applied to the I/Os must not power up any part of the device.
3. VCCI should not exceed 3.6 V, per datasheet specifications.

As described in the "Power-Up to Functional Time" section on page 312, Microsemi's low power flash I/Os are tristated before and during power-up until the last voltage supply (VCC or VCCI) is powered up past its functional level. Furthermore, applying voltage to the FPGA I/Os does not pull up VCC or VCCI and, therefore, does not partially power up the device. Table 17-4 includes the cold-sparing test results on A3PE600-PQ208 devices. In this test, leakage current on the device I/O and residual voltage on the power supply rails were measured while voltage was applied to the I/O before power-up.

***Table 17-4* • Cold-Sparing Test Results for A3PE600 Devices**

Device I/O	Residual Voltage (V)		Leakage Current
	VCC	VCCI	
Input	0	0.003	<1 µA
Output	0	0.003	<1 µA

VCCI must not exceed 3.6 V, as stated in the datasheet specification. Therefore, ProASIC3E devices meet all three requirements stated earlier in this section and are suitable for cold-sparing applications.

The following devices and families support cold-sparing:

- IGLOO: AGL015 and AGL030
- All IGLOO nano
- All IGLOO PLUS
- All IGLOOe
- ProASIC3L: A3PE3000L
- ProASIC3: A3P015 and A3P030
- All ProASIC3 nano
- All ProASIC3E
- Military ProASIC3EL: A3PE600L and A3PE3000L
- RT ProASIC3: RT3PE600L and RT3PE3000L